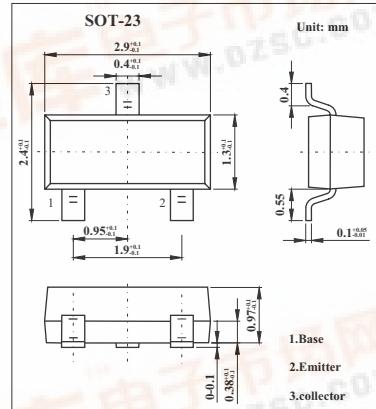


SMD Type

Transistors

PNP General Purpose Amplifier

BSS63



■ Features

- PNP general purpose amplifier

■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-emitter voltage	V _{CE0}	100	V
Collector-base voltage	V _{CBO}	110	V
Emitter-base voltage	V _{EBO}	6	V
Collector current	I _C	200	mA
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C
Total device dissipation	P _D	350	mW
Derate above 25°C		2.8	mW/°C
Thermal resistance, junction to ambient	R _{θJA}	357	°C/W

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = 100 μA, I _B = 0	100			V
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = 10 μA, I _E = 0	110			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = 1.0 μA, I _C = 0	6			V
Collector-cutoff current	I _{CBO}	V _{CB} = 90 V, I _E = 0			100	nA
		V _{CB} = 90 V, I _E = 0, T _A = 150°C			50	μA
Emitter-base cut-off current	I _{EBO}	V _{EB} = 6.0 V, I _C = 0			200	nA
DC current gain	h _{FE}	I _C = 10 mA, V _{CE} = 1.0 V	30			
		I _C = 25 mA, V _{CE} = 1.0 V	30			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = 25 mA, I _B = 2.5 mA			0.25	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C = 25 mA, I _B = 2.5 mA			0.9	V
Current gain - bandwidth product	f _T	I _C = 25 mA, V _{CE} = 5.0, f = 35 MHz	50			MHz

■ Marking

Marking	T3
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